



44 2823/
Docket No. 0756-1998
Amended
#30/R/EXT
10/24/02
MS

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

) Art Unit: 2823

Shunpei YAMAZAKI et al.

) Examiner: F. Toledo

Serial No. 09/352,194

)

Filed: July 13, 1999

)

For: CRYSTALLINE SEMICONDUCTOR

)

THIN FILM, METHOD OF FABRICATING

)

THE SAME, SEMICONDUCTOR DEVICE,

)

AND METHOD OF FABRICATING THE

)

SAME

)

<p align="center">CERTIFICATE OF MAILING</p> <p>I hereby certify that this correspondence is being deposited with The United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Commissioner for Patents, Washington, D.C. 20231, on <u>10/24/02</u></p> <p><i>[Signature]</i></p>

AMENDMENT

Honorable Commissioner of Patents

Washington, D.C. 20231

Sir:

In response to the Office Action dated June 5, 2002 please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claims 5, 36-48 and 56 as follows:

5. (Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film comprising silicon over a substrate;

providing said semiconductor film with a catalytic element for facilitating a crystallization of said semiconductor film;

irradiating said semiconductor film with laser light in air for crystallizing said semiconductor film after providing said catalytic element;

removing an oxide film from a surface of said semiconductor film by etching after said irradiation of said laser light;

leveling said surface of said semiconductor film by heating after removing said oxide film; and

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